

Small switching (60V, 10A)

2SK2095N

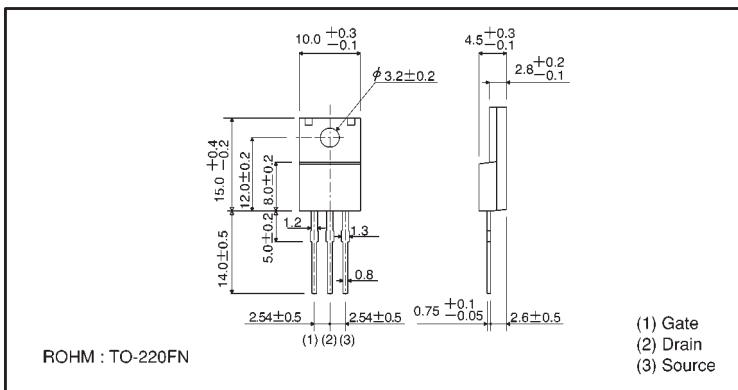
●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Easily designed drive circuits.
- 5) Low $V_{GS(th)}$.
- 6) Easy to parallel.

●Structure

Silicon N-channel
MOSFET

●External dimensions (Units: mm)



●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	± 20	V
Drain current	Continuous	I_D	10
	Pulsed	I_{DP}^*	40
Reverse drain current	Continuous	I_{DR}	10
	Pulsed	I_{DRP}^*	40
Total power dissipation ($T_c=25^\circ\text{C}$)	P_D	30	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

* $P_w \leq 10 \mu\text{s}$, Duty cycle $\leq 1\%$

●Packaging specifications

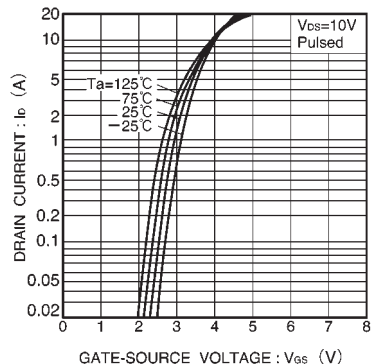
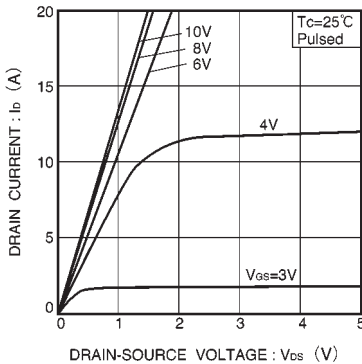
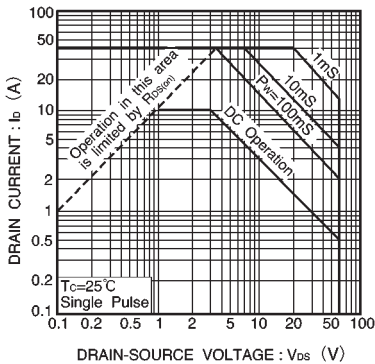
Type	Package	Bulk
	Code	—
	Basic ordering unit (pieces)	500
2SK2095N		○

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Gate-source leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	—	—	100	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	—	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}$	—	0.080	0.095	Ω	$I_D = 5A, V_{GS} = 10V$
		—	0.11	0.14		$I_D = 5A, V_{GS} = 4V$
Forward transfer admittance	$ Y_{fs} ^*$	5.0	—	—	S	$I_D = 5A, V_{DS} = 10V$
Input capacitance	C_{iss}	—	1600	—	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	—	600	—	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	—	150	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = 5A, V_{DD} \div 30V$
Rise time	t_r	—	80	—	ns	$V_{GS} = 10V$
Turn-off delay time	$t_{d(off)}$	—	300	—	ns	$R_L = 6\Omega$
Fall time	t_f	—	100	—	ns	$R_G = 10\Omega$

* $P_w \leq 300 \mu s$, Duty cycle $\leq 1\%$

●Electrical characteristic curves



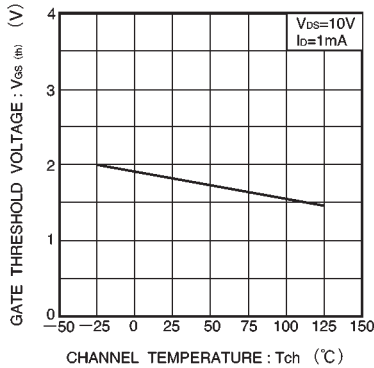


Fig.4 Gate threshold voltage vs. channel temperature

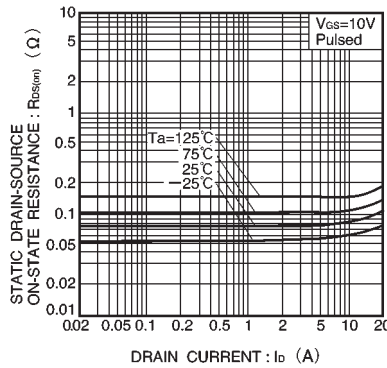


Fig.5 Static drain-source on-state resistance vs. drain current (I)

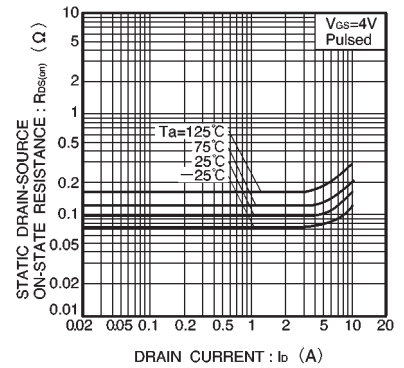


Fig.6 Static drain-source on-state resistance vs. drain current (II)

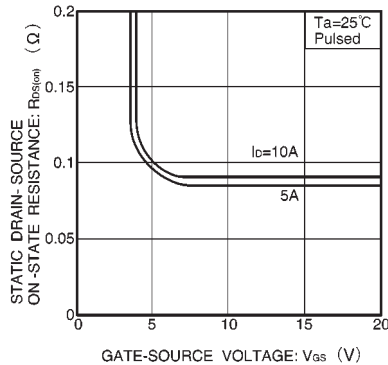


Fig.7 Static drain-source on-state resistance vs. gate-source voltage

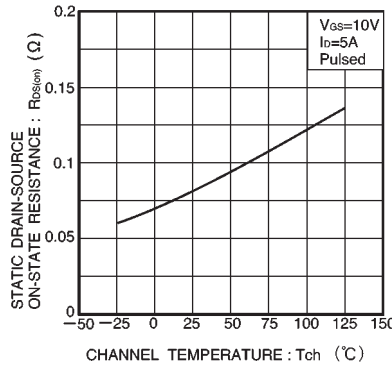


Fig.8 Static drain-source on-state resistance vs. channel temperature

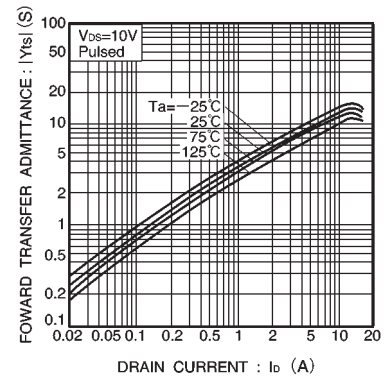


Fig.9 Forward transfer admittance vs. drain current

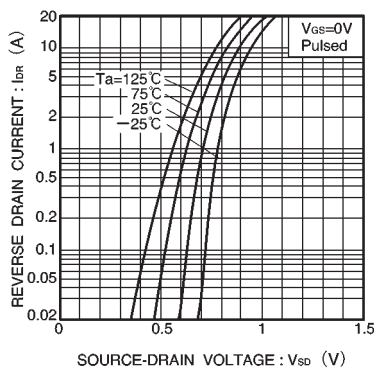


Fig.10 Reverse drain current vs. source-drain voltage (I)

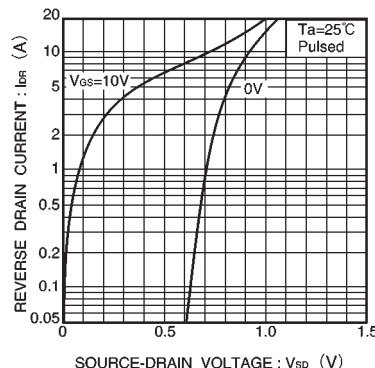


Fig.11 Reverse drain current vs. source-drain voltage (II)

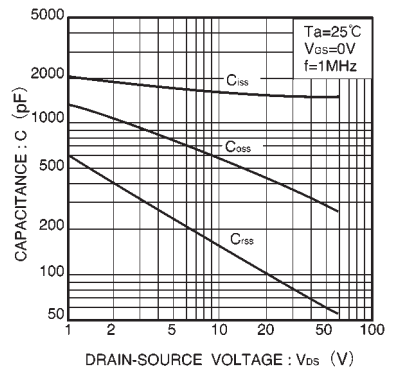


Fig.12 Typical capacitance vs. drain-source voltage

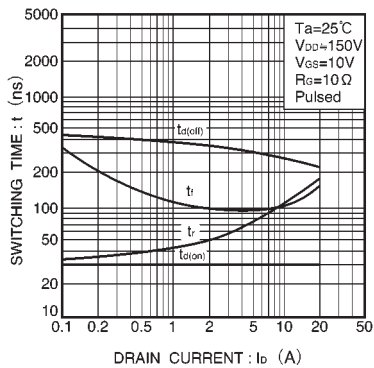


Fig.13 Switching characteristics
(See Figures 15 and 16 for the measurement circuit and resultant waveforms.)

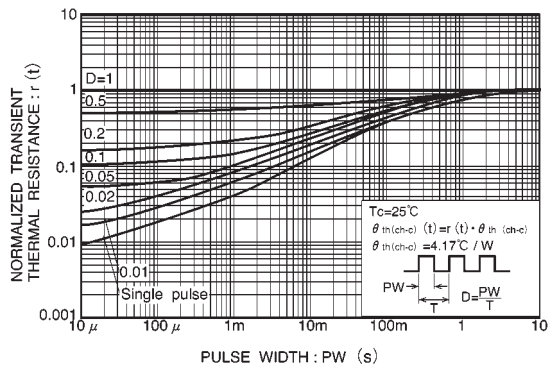


Fig.14 Normalized transient thermal resistance vs. pulse width

● Switching characteristics measurement circuit

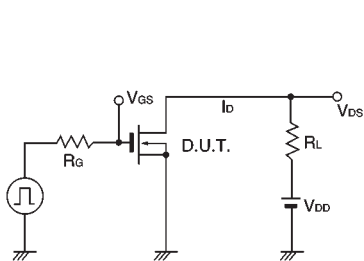


Fig.15 Switching time measurement circuit

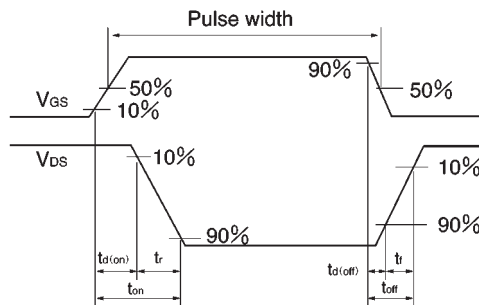


Fig.16 Switching time waveforms